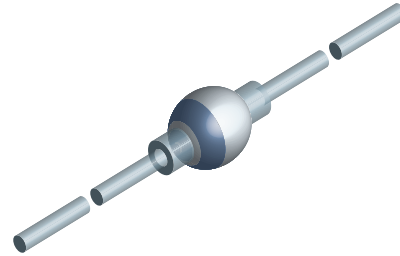


## Fast Sinterglass Diode

### Features

- High temperature metallurgically bonded construction
- Cavity-free glass passivated junction
- Fast switching for high efficiency
- 3.0 ampere operation at  $T_{amb} = 50\text{ }^{\circ}\text{C}$  with no thermal runaway
- Hermetically sealed package



17133

### Mechanical Data

**Case:** Sintered glass case, G4

**Terminals:** Solder plated axial leads, solderable per MIL-STD-750, Method 2026

**Mounting Position:** Any

**Weight:** 1040 mg

### Parts Table

Part	Type differentiation	Package
RG4A	$V_{RRM} = 50\text{ V}$	G4
RG4B	$V_{RRM} = 100\text{ V}$	G4
RG4D	$V_{RRM} = 200\text{ V}$	G4
RG4G	$V_{RRM} = 400\text{ V}$	G4
RG4J	$V_{RRM} = 600\text{ V}$	G4

### Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Reverse voltage = Repetitive peak reverse voltage	see electrical characteristics	RG4A	$V_R = V_{RRM}$	50	V
	see electrical characteristics	RG4B	$V_R = V_{RRM}$	100	V
	see electrical characteristics	RG4D	$V_R = V_{RRM}$	200	V
	see electrical characteristics	RG4J	$V_R = V_{RRM}$	400	V
	see electrical characteristics	RG1J	$V_R = V_{RRM}$	600	V
Maximum average forward rectified current	0.375 " (9.5 mm) lead length at $T_{amb} = 55\text{ }^{\circ}\text{C}$		$I_{F(AV)}$	3.0	A
Peak forward surge current	8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)		$I_{FSM}$	100	A
Maximum average reverse current	at rated peak reverse voltage $T_{amb} = 25\text{ }^{\circ}\text{C}$		$I_{R(AV)}$	2.0	$\mu\text{A}$
	at rated peak reverse voltage $T_{amb} = 100\text{ }^{\circ}\text{C}$		$I_{R(AV)}$	100	$\mu\text{A}$
Operating junction and storage temperature range			$T_J$	-55 to +	$^{\circ}\text{C}$
			$T_{STG}$	175	

## Maximum Thermal Resistance

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Typical thermal resistance <sup>1)</sup>	$R_{\theta JA}$	22	K/W

<sup>1)</sup> Thermal resistance from junction to ambient at 0.375 " (9.5 mm) lead length, with both leads attached to heat sink

## Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Part	Symbol	Typ.	Max	Unit
Maximum instantaneous forward voltage	$I_F = 3.0\text{ A}$		$V_F$		1.3	V
Maximum reverse current	$V_R = V_{RRM}$		$I_R$		5.0	$\mu\text{A}$
Maximum reverse recovery time	$I_F = 0.5\text{ A}, I_R = 1.0\text{ A}, I_{rr} = 0.25\text{ A}$	RG4A	$t_{rr}$		150	ns
	$I_F = 0.5\text{ A}, I_R = 1.0\text{ A}, I_{rr} = 0.25\text{ A}$	RG4B	$t_{rr}$		150	ns
	$I_F = 0.5\text{ A}, I_R = 1.0\text{ A}, I_{rr} = 0.25\text{ A}$	RG4D	$t_{rr}$		150	ns
	$I_F = 0.5\text{ A}, I_R = 1.0\text{ A}, I_{rr} = 0.25\text{ A}$	RG4G	$t_{rr}$		150	ns
	$I_F = 0.5\text{ A}, I_R = 1.0\text{ A}, I_{rr} = 0.25\text{ A}$	RG4J	$t_{rr}$		250	ns
Typical junction capacitance	$V_R = 4.0\text{ V}, f = 1\text{ MHz}$		$C_J$	50		pF

## Typical Characteristics ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

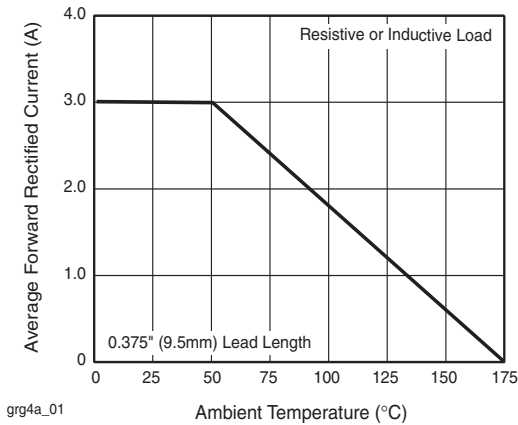


Figure 1. Forward Current Derating Curve

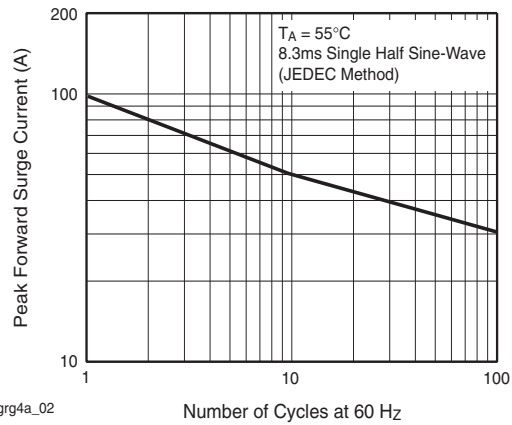


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current

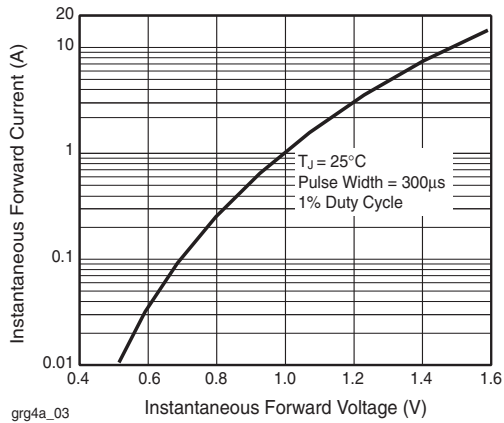


Figure 3. Typical Instantaneous Forward Characteristics

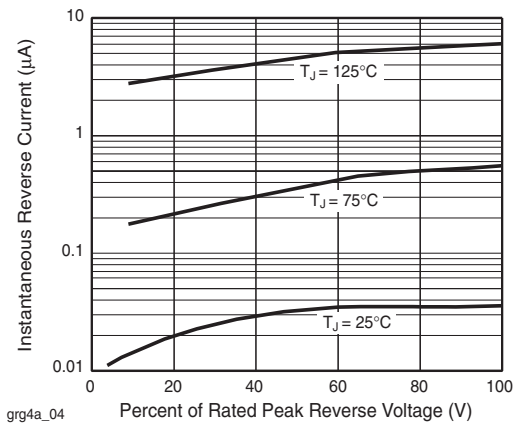


Figure 4. Typical Reverse Characteristics

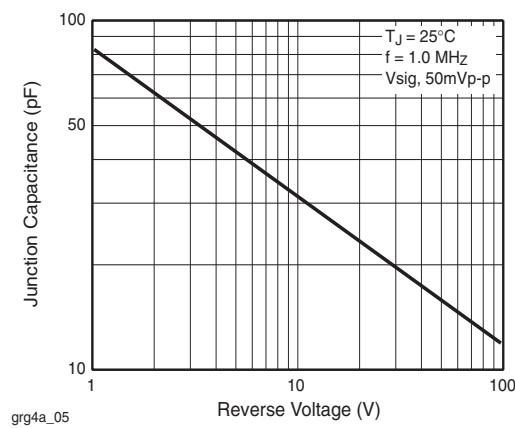


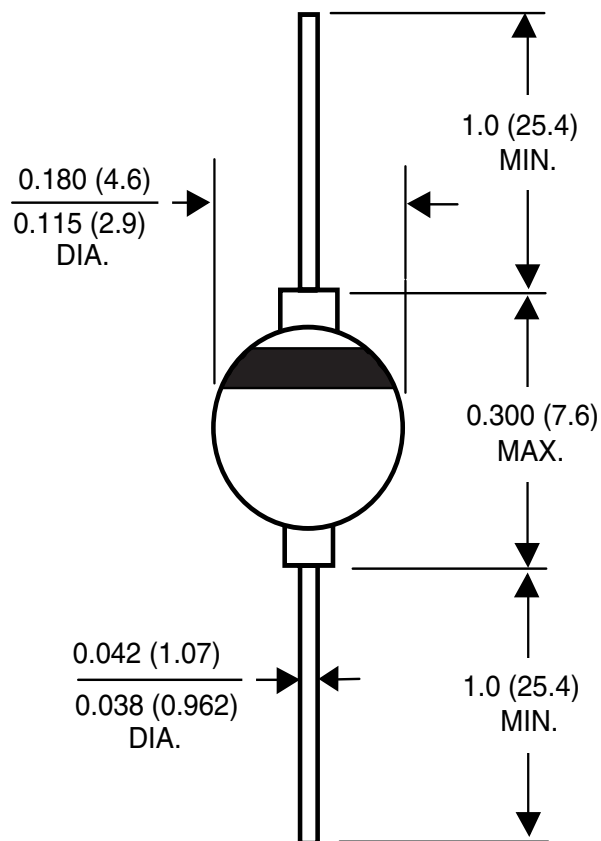
Figure 5. Typical Junction Capacitance

# RG4A to RG4J

Vishay Semiconductors



## Package Dimensions in Inches (mm)



17032



## Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Vishay Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Vishay Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design  
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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